Temperature Compensated Crystal Oscillator (TCXO)

- · Package size (3.2 mm × 2.5 mm × 0.9 mm)
- · High stability TCXO
- · Output waveform : CMOS
- · Reference weight Typ. 26 mg

[1] Product Number / Product Name

(1-1) Product Number / Ordering Code

X1G0051010026xx

last 2 digits code(xx) define Quantity. The standard is "00", 2 000 pcs/Reel.

(1-2) Product Name / Model Name

TG3225CEN 24.000000 MHz KFGNNM

[2] Operating Conditions

Parameter	Cumbal	Ç	Specification	S	Unit	Conditions	
Farameter	Symbol	Min.	Тур.	Max.	Offic	Conditions	
Supply voltage	Vcc	2.375	-	3.63	V	-	
Supply voltage	GND	0	-	0	V	-	
Operating temperature range	T_use	-40	-	+85	°C	-	
Output load	Load_C	13.5	15	16.5	pF	-	

[3] Frequency Characteristics

 $(Vcc = 2.375 to 3.63 V, GND = 0.0 V, Load = 15 pF, T_use = +25 °C)$

			•			
Parameter	Symbol		Specification	S	Unit	Conditions
raiailletei	Syllibol	Min.	Тур.	Max.	Offic	Cortainoris
Output Frequency	fo	-	24	-	MHz	
Frequency tolerance *1	f_tol	-2.0	-	+2.0	x10 ⁻⁶	T_use = +25 °C±2 °C After 2 reflows *2
Frequency / temperature characteristics	fo-Tc	-2.0	ı	+2.0	x10 ⁻⁶	T_use = -40 °C to +85 °C (Reference to +25 °C)
Frequency / load coefficient	fo-Load	-0.2	-	+0.2	x10 ⁻⁶	15 pF±10 %
Frequency / voltage coefficient	fo-Vcc	-0.3	ı	+0.3	x10 ⁻⁶	Vcc ±5 % *3
Frequency aging *4	f_age	-1.0	-	+1.0	x10 ⁻⁶	T_use = +25°C first year

^{*1} Include initial frequency tolerance and frequency deviation after reflow cycles.

[4] Electrical Characteristics

(Vcc = 2.375 to 3.63 V, GND = 0.0 V, Load = 15 pF, T_use = +25 °C)

Parameter	Symbol	Ş	Specification	S	Unit	Conditions	
Farameter	Symbol	Min.	Тур.	Max.	Offic	Conditions	
Current consumption	Icc	-	-	4.0	mA	-	
Output voltage	Voн	90 % Vcc	ı	-	V	-	
Output voltage	Vol	-	ı	10 % Vcc	V	-	
Rise time	tr	-	ı	8	ns	10 % Vcc to 90 % Vcc level	
Fall time	tf	ı	ı	8	ns	90 % Vcc to 10 % Vcc level	
Start up time	t str	-	ı	2.0	ms	Until frequency has been reached within ±1x10 ⁻⁶ of final frequency.	
		-	-	2.0	ms	Until output signal has been reached min 90 % of final amp.	
Symmetry	SYM	45	50	55	%	50 % Vcc Level	

[For other general specifications, please refer to the attached Full Data Sheet below]

^{*2} Measured in the elapse of 24 hours after reflow soldering.

^{*3} Vcc ± 5% must be in operating supply voltage range (3 V to 3.6 V)

^{*4} Aging stability is estimated from environmental reliability tests; expected amount of the frequency variation.



High stability temperature compensated crystal oscillator Product name: TG3225CEN / TG2520CEN

Features

High stability

• Frequency range: 12 MHz to 52 MHz

Output : CMOS

Supply voltage : 2.375 to 3.63 V

External dimensions: 3.2 x 2.5 x 0.9mm

 $: 2.5 \times 2.0 \times 0.8 \text{ mm}$

Small size package (4pads)

Pb free.

Complies with EU RoHS directive.

Applications

- Measurement machine
- Wireless communication devices
- Smart meter
- Telemeter etc..

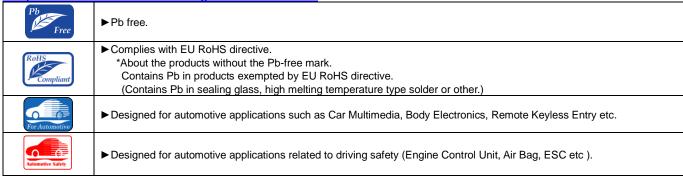


Description

These products are high stability temperature compensated crystal oscillator of CMOS outputs using fundamental oscillation of Crystal unit.

This has realized a low phase noise in frequency 12 to 52 MHz, and it is suitable for the reference clock for measurement machine and wireless communication devices.

Explanation of the mark that are using it for the documents



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/ Space equipment (artificial satellites, rockets, etc.) / Transportation vehicles and related (automobiles, aircraft, trains, vessels, etc.) / Medical instruments to sustain life / Submarine transmitters / Power stations and related / Fire work equipment and security equipment / traffic control equipment / and others requiring equivalent reliability.

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1. Electrical characteristics

1) Absolute maximum ratings

Parameter	Symbol	Unit	Min.	Тур.	Max	Notes
Supply voltage	Vcc-GND	V	-0.5	-	+4.0	
Storage temperature	T_stg	°C	-40	-	+90	Store as bare product after packing
Frequency control voltage	Vc-GND	V	-0.5	-	Vcc+0.5	V _C Terminal

2) Operating conditions

Demander of the control of the contr		1.1:4	N 4:	T	N 4 - · ·	NI-4
Parameter	Symbol	Unit	Min.	Тур.	Max	Notes
			2.375	-	3.63	Supply voltage range
	Vcc		2.66	2.8	2.94	V _{CC} =2.8 V Type
Supply voltage	VCC	V	2.85	3.0	3.15	Vcc=3.0 V Type
			3.135	3.3	3.465	Vcc=3.3 V Type
	GND		0.0	-	0.0	
Operating temperature range	T_use	°C	-40	+25	+85	
			GND	N.C.	-	V _C Terminal / TCXO
Fraguency control voltage	V/a	V	0.4	1.4	2.4	
Frequency control voltage	Vc	٧	0.5	1.5	2.5	V _C Terminal / VC-TCXO
			0.65	1.65	2.65	
Output load condition	Load_C	pF	13.5	15	16.5	

3-1) Frequency characteristics (Vcc=Typ., GND=0.0 V, Vc=Typ. V, Load=Typ., T_use=+25°C)

3-1) Frequency chara	Š	(Vcc=Typ.,	GND=0.0 V	Vc=Typ. V, Load=Typ., T_use=+25°C)		
Parameter	Symbol	Unit	Min.	Тур.	Max	Notes
Output frequency	fo	MHz	12	-	52	
Frequency tolerance *1 (T_use=+25°C +/-2°C)	f tol	× 10 ⁻⁶	-2.0	-	+2.0	(Standard)
(Reflow cycles : 2 times) *2	1_101	X 10	-1.5	-	+1.5	(Option)
Frequency / temperature characteristics (Reference to +25°C.)	fo-Tc	× 10 ⁻⁶	-2.0	-	+2.0	T_use=-40°C to +85°C
Frequency / load coefficient	fo-Load	× 10 ⁻⁶	-0.2	-	+0.2	Load +/-10%
Frequency / voltage coefficient	fo- V _{CC}	× 10 ⁻⁶	-0.3	-	+0.3	V _{CC} +/-5% *3
Hysteresis	-	× 10 ⁻⁶	-0.6	-	+0.6	Frequency measured before and after at +25°C.
			-1.0	-	+1.0	T_use=+25°C, First year (Standard)
			-0.7	-	+0.7	T_use=+25°C, First year (Option)
Frequency aging			-2.0	-	+2.0	T_use=+25°C, 3 years (Standard)
(12 MHz ≤ f0 ≤ 20 MHz,	f_age	× 10 ⁻⁶	-1.5	-	+1.5	T_use=+25°C, 3 years (Option)
$24 \text{ MHz} \le 60 \le 40 \text{ MHz})$	i_age	^ 10	-3.0	-	+3.0	T_use=+25°C, 5 years (Standard)
24 WH 12 = 10 = 40 WH 12)			-2.0	-	+2.0	T_use=+25°C, 5 years (Option)
			-5.0	-	+5.0	T_use=+25°C, 10 years (Standard)
			-3.5	-	+3.5	T_use=+25°C, 10 years (Option)
Frequency aging			-1.5	-	+1.5	T_use=+25°C, First year
Frequency aging (20 MHz < f0 < 24 MHz,	f_age	× 10 ⁻⁶	-2.5	-	+2.5	T_use=+25°C, 3 years
40 MHz < f0 ≤ 52 MHz)	i_aye		-3.0	-	+3.0	T_use=+25°C, 5 years
40 MH2 < 10 \(52 MH2)	I		-5.0	-	+5.0	T_use=+25°C, 10 years

^{*1} Include initial frequency tolerance and frequency deviation after reflow cycles.

3-2) Frequency control characteristics (Vcc=Typ., GND=0.0 V, Vc=Typ. V, Load=Typ., T_use=+25°C)

-,					,	
Parameter	Symbol	Unit	Min.	Тур.	Max	Notes
Frequency control range	f cont	× 10 ⁻⁶	-15.0	-	-8.0	Vc=1.4V+/-1.0V, Vc=1.5V+/-1.0V,
Frequency control range	I_COIT	X 10 °	+8.0	-	+15.0	Vc=1.65V+/-1.0V
Linearity	-	%	-10	-	+10	
Input impedance	Z _{IN}	kΩ	500	-	-	Vc-GND(DC), Vc=Typ.
Frequency change polarity	-	-	P	ositive polari	ty	

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^{*2} Measured in the elapse of 24 hours after reflow soldering.

^{*3} Vcc +/- 5% must be in operating supply voltage range.



4) Electrical Characteristics (Vcc=Typ., GND=0.0 V, Vc=Typ. V, Load=Typ., T_use=+25°C) Unit Parameter Symbol Min. Max Notes Тур. 12 MHz ≤ f0 ≤ 26 MHz 4.0 6.0 26 MHz <f0 ≤ 39 MHz Current consumption mΑ Icc 39 MHz <<u>f0 ≤ 52 MHz</u> 6.5 Until output signal has been reached 2.0 _ min 90% of final amp. Start up time t_str ms Until frequency has been reached within +/-1x10⁻⁶ of final frequency.

10%Vcc to 90%Vcc level (Standard) 2.0 8.0 Rise time tr ns 6.5 10%Vcc to 90%Vcc level (Option) 8.0 90%Vcc to 10%Vcc level (Standard) --Fall time tf ns 6.5 90%Vcc to 10%Vcc level (**Option**) SYM % 45 50 50%Vcc level Symmetry 55 ٧ 90% Vcc High output voltage Vон 10% Vcc V_{OL} Low output voltage ٧ -68 -54 1 Hz offset -98 -86 10 Hz offset 100 Hz offset -123 -113 Phase noise dBc/ L(f) -144 -136 1 kHz offset (12MHz) Hz -152 -146 10 kHz offset -152 -146 100 kHz offset -147 1 MHz offset -153 -60 -46 1 Hz offset -91 -79 10 Hz offset -117 -107 100 Hz offset Phase noise dBc/ L(f) -139 -131 1 kHz offset (27MHz) Hz -145 -151 10 kHz offset -147 100 kHz offset -153 1 MHz offset -155 -149 1 Hz offset -59 -45 -89 -77 10 Hz offset -115 -105 100 Hz offset dBc/ Phase noise L(f) -136 -128 1 kHz offset (39MHz) Hz -149 -143 10 kHz offset -151 -145 100 kHz offset -147 -153 1 MHz offset -55 -41 1 Hz offset -85 -73 10 Hz offset -112 -102 100 Hz offset Phase noise dBc/ L(f) -133 -125 1 kHz offset (52MHz) Hz --147 -142 10 kHz offset -144

-150

-152

-146

100 kHz offset

1 MHz offset

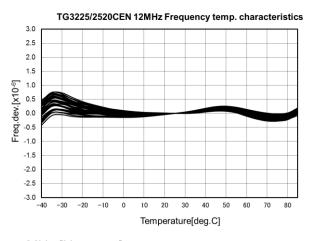


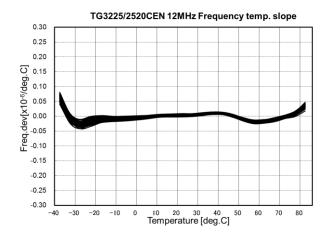
2. Characteristics

2-1) "Frequency / temperature characteristics"

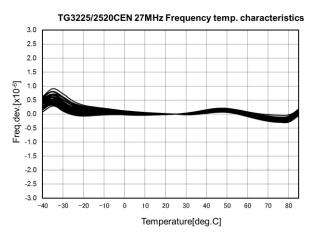
2-1-1) Standard spec : $\pm 1.0^{-6}$ Max. (T_use=-40°C to $\pm 85^{\circ}$ C)

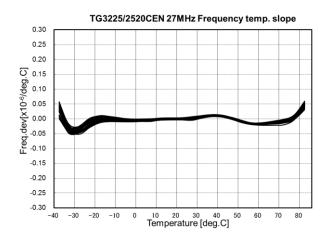
12MHz [N=40pcs]



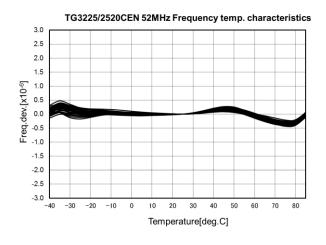


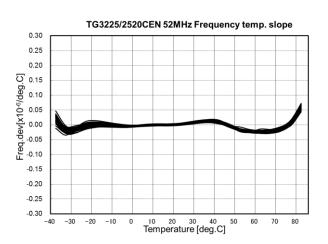
27MHz [N=40pcs]





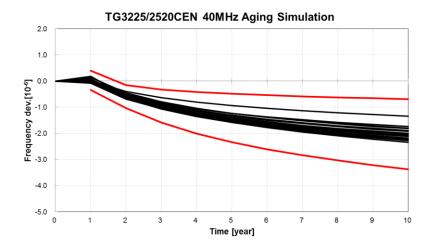
52MHz [N=40pcs]







2-2) Frequency aging (40MHz) [N=22pcs]



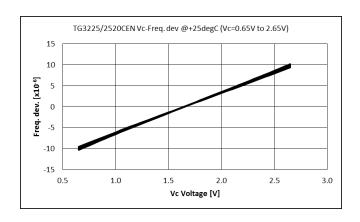
about 1year

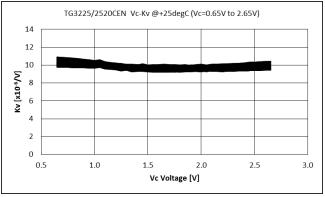
Ave. : +0.03 x 10⁻⁶ Max. : +0.19 x 10⁻⁶ Min. : -0.08 x 10⁻⁶

about 10years

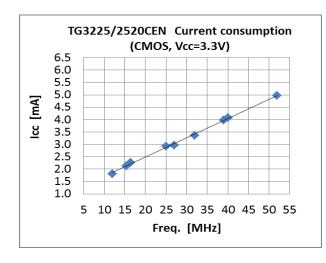
Ave. : -2.03×10^{-6} Max. : -1.34×10^{-6} Min. : -2.34×10^{-6}

2-3) Frequency control characteristics [N=40pcs]

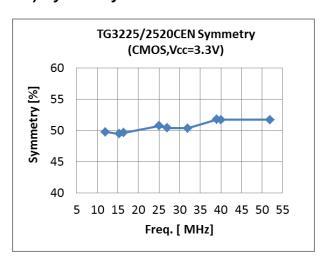




2-4) current consumption

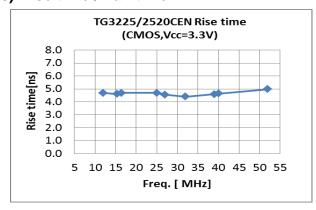


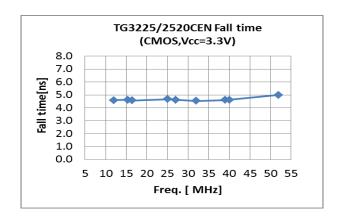
2-5) Symmetry



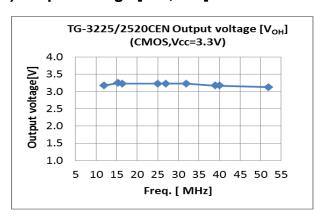


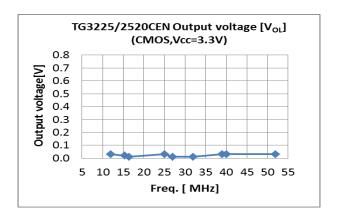
2-6) Rise time / Fall time





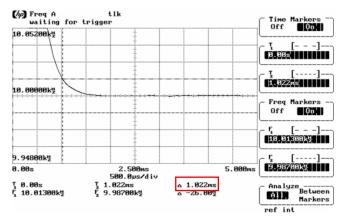
2-7) Output voltage [Voh, Vol]



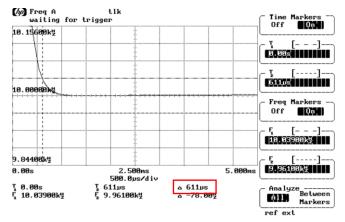


2-8) start up time(27MHz, 39MHz, 52MHz)

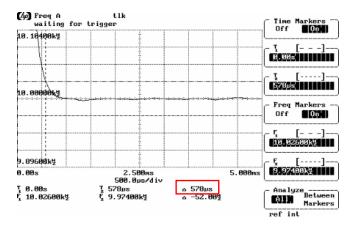
27MHz



39MHz

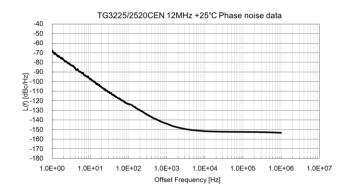


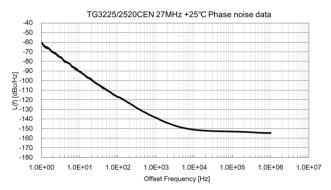
52MHz

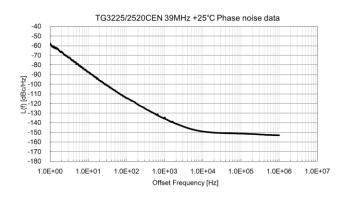


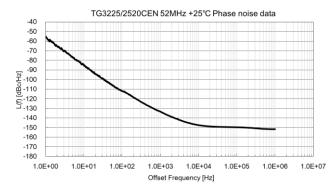


2-9) Phase noise (12MHz, 27MHz, 39MHz, 52MHz, refer to data of Page3.)

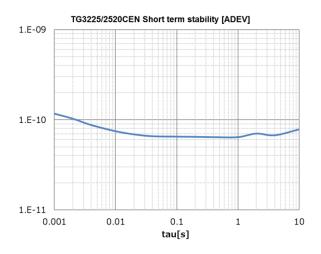








2-10) Short term stability [ADEV] (27MHz)

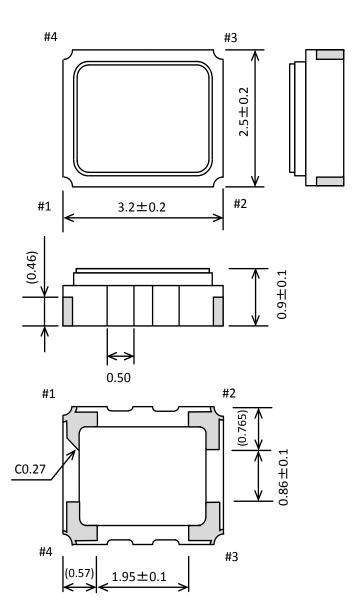




3. Outline

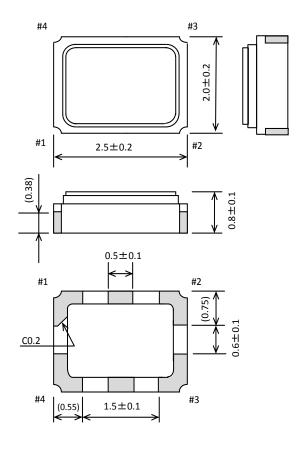
3-1) Outline dimensions and Pin information

3-1-1) TG3225CEN



3-1-2) TG2520CEN

Unit: mm



Pin	Connec	tions					
Ī	VC-TCXO	TCXO					
1	Vc	N.C.					
2	GND						
3	OUT						
4	V _{cc}						

Do not connect "N.C." pin with any other leads (also mutually)

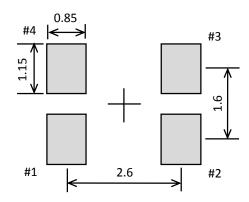
Material Ceramics(Cavity) Au plated nickel(Electric terminal) Fe-Ni-Co(Lid)



3-2) Soldering pattern

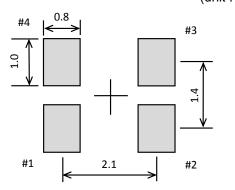
Example of patterning design indicated as follows. In an actual design, please consider mounting density, the reliability of soldering, etc. and check whether performance is optimal.

3-2-1) TG3225CEN



3-2-2) TG2520CEN

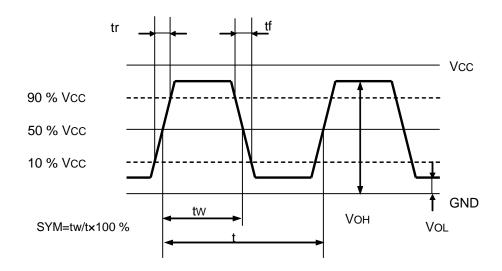
(unit: mm)



To maintain stable operation, provide a 0.01 to 0.1uF by-pass capacitor at a location as near as possible to the power source terminal of the crystal product (between Vcc - GND).

4. Timing chart

4-1) Output waveform (CMOS output)



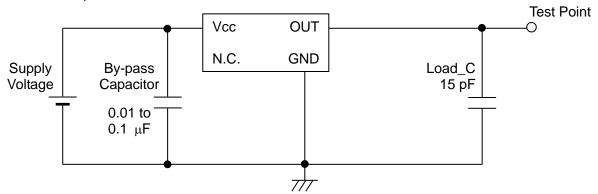
9 / 13



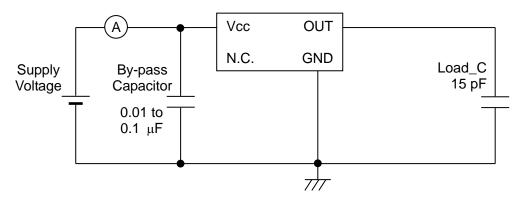
5. Test circuit

5-1) CMOS output for TCXO

1) Output Load: 15 pF



2) Current consumption



3) Conditions

1. Oscilloscope: Impedance Min. 1 M Ω Input capacitance Max. 10 pF Band width Min. 300 MHz

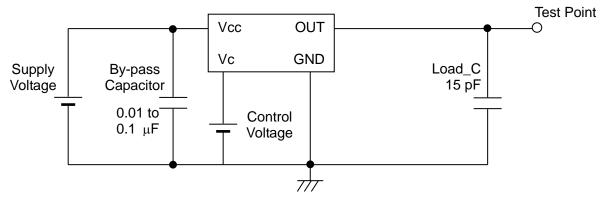
Impossible to measure both frequency and wave form at the same time.(In case of using oscilloscope's amplifier output, possible to measure both at the same time.)

- 2. Load_C includes probe capacitance.
- 3. A capacitor (By-pass: 0.01 to 0.1 $\,\mu F$) is placed between V_{CC} and GND, and closely to TCXO.
- 4. Use the current meter whose internal impedance value is small.
- Power Supply Impedance of power supply should be as low as possible.
- 6. GND pin should be connected to low impedance GND.

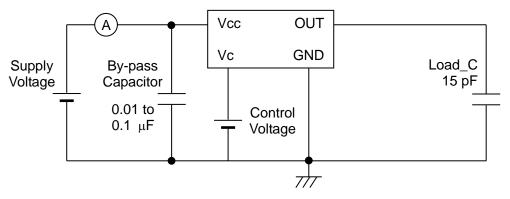


5-2) CMOS output for VC-TCXO

1) Output Load: 15 pF



2) Current consumption



3) Conditions

1. Oscilloscope: Impedance Min. 1 M Ω Input capacitance Max. 10 pF Band width Min. 300 MHz

Impossible to measure both frequency and wave form at the same time.(In case of using oscilloscope's amplifier output, possible to measure both at the same time.)

- 2. Load_C includes probe capacitance.
- 3. A capacitor (By-pass: 0.01 to 0.1 $\,\mu F$) is placed between V_{CC} and GND, and closely to TCXO.
- 4. Use the current meter whose internal impedance value is small.
- Power Supply
 Impedance of power supply should be as low as possible.
- 6. GND pin should be connected to low impedance GND.

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6. Handling precautions

Prior to using this product, please carefully read the section entitled "Precautions" on our Web site (http://www5.epsondevice.com/en/quartz/tech/precaution/) for instructions on how to handle and use the product properly to ensure optimal performance of the product in your equipment. Before using the product under any conditions other than those specified therein, please consult with us to verify and confirm that the performance of the product will not be negatively affected by use under such conditions.

In addition to the foregoing precautions, in order to avoid the deteriorating performance of the product, we strongly recommend that you <u>DO NOT</u> use the product under <u>ANY</u> of the following conditions:

- (1) Mounting the product on a board using water-soluble solder flux and using the product without removing the residue of the flux completely from the board. The residue of such flux that is soluble in water or water-soluble cleaning agent, especially the residues which contains active halogens, will negatively affect the performance and reliability of the product.
- (2) Using the product in any manner that will result in any shock or impact to the product.
- (3) Using the product in places where the product is exposed to water, chemicals, organic solvent, sunlight, dust, corrosive gasses, or other materials.
- (4) Using the product in places where the product is exposed to static electricity or electromagnetic waves.
- (5) Applying ultrasonic cleaning without advance verification and confirmation that the product will not be affected by such a cleaning process, because it may damage the crystal, IC and/or metal line of the product.
- (6) Touching the IC surface with tweezers or other hard materials directly.
- (7) Using the product under any other conditions that may negatively affect the performance and/or reliability of the product.
- (8) Power supply with ripple may cause of incorrect operation or degradation of phase noise characteristics, so please evaluate before use.
- (9) Frequency aging is from environmental tests results to the expectation of the amount of the frequency variation. This doesn't guarantee the product-life cycle.
- (10) This components used underfill material at the back side of package.
 After mounting this components on the board, there's possibility of IC damage happened by thermal expansion of adhesive, if adhesive will break into between TCXO and the board.

Please do not use adhesive, this will cause oscillation stop in case of IC damaged by adhesive.

Should any customer use the product in any manner contrary to the precautions and/or advice herein, such use shall be done at the customer's own risk.

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Document No.: TG3225_2520CEN_AE_Ver. 1.00
Date: Nov. 20th 2017



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